FC694301

Silicon N-channel MOS FET

For switching circuits

Overview

FC694301 is dual N-channel small signal MOS FET employed small size surface mounting package.

■ Features

- High-speed switching
- Low drain-source ON resistance: $R_{DS(on)}$ typ. = 3 Ω (V_{GS} = 2.5 V)
- Small size surface mounting package: SSMini6-F3-B
- Eco-friendly Halogen-free package

■ Packaging

FC6943010R Embossed type (Thermo-compression sealing): 8000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit
FET1 FET2	Drain-source surrender voltage	V _{DSS}	30	V
	Gate-source surrender voltage	V _{GSS}	±12	V
	Drain current	I_D	100	mA
	Peak drain current	I_{DP}	200	mA
Overall	Total power dissipation	P_{T}	125	mW
	Channel temperature	T _{ch}	150	°C
	Storage temperature	T _{stg}	-55 to +150	°C

■ Package

• Code

SSMini6-F3-B

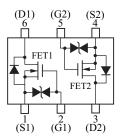
Package dimension clicks here.→

• Pin Name

1: Source (FET1) 4: Source (FET2) 2: Gate (FET1) 5: Gate (FET2) 3: Drain (FET2) 6: Drain (FET1)

■ Marking Symbol: V4

■ Internal Connection



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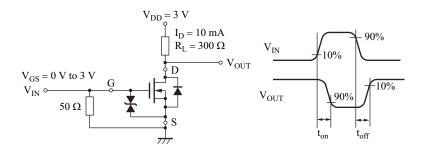
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■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	30			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0$			1.0	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$			±10	μА
Gate threshold voltage	V _{TH}	$I_D = 1.0 \mu A, V_{DS} = 3.0 \text{ V}$	0.5	1.0	1.5	V
Drain-source ON resistance	R _{DS(on)}	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		3	6	Ω
Diani-source On Tesistance		$I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$		2	3	Ω
Forward transfer admittance	Yfs	$I_D = 10 \text{ mA}, V_{DS} = 3.0 \text{ V}$	20	55		mS
Short-circuit input capacitance (Common source)	C _{iss}			12		pF
Short-circuit output capacitance (Common source)	C _{oss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		7		pF
Reverse transfer capacitance (Common source)	C _{rss}			3		pF
Turn-on time *	t _{on}	$V_{DD} = 3 \text{ V}, V_{GS} = 0 \text{ V to 3 V},$ $R_L = 300 \Omega$		100		ns
Turn-off time *	t _{off}	$V_{DD} = 3 \text{ V}, V_{GS} = 3 \text{ V to } 0 \text{ V},$ $R_L = 300 \Omega$		100		ns

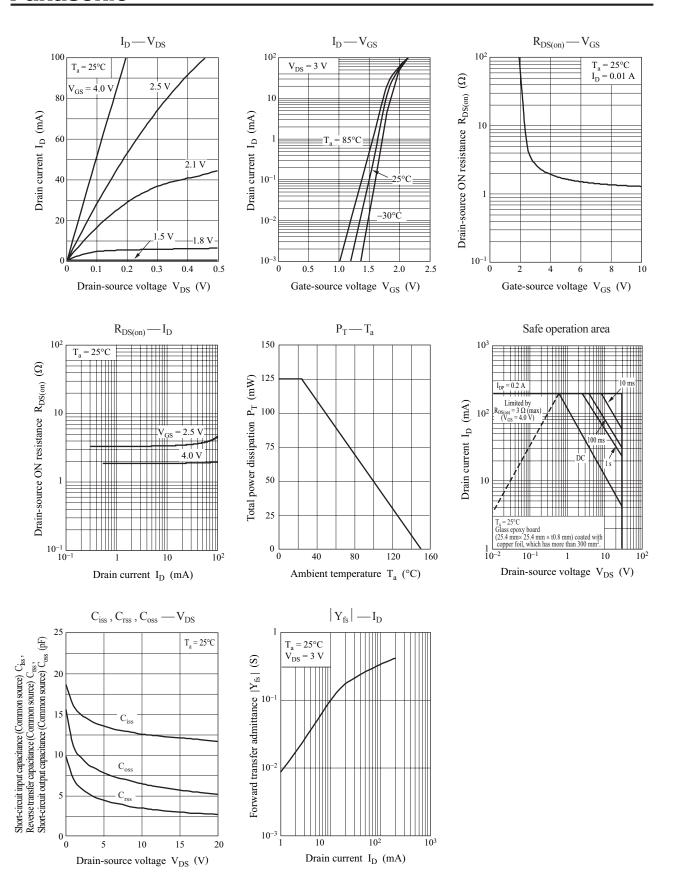
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Test circuit



2 Ver. DED

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